編號: 177

國立成功大學 106 學年度碩士班招生考試試題

系 所:電機工程學系 考試科目:電子材料概論

考試日期:0213, 節次:2

第1頁,共/頁

※ 考生請注意:本試題不可使用計算機。 請於答案卷(卡)作答,於本試題紙上作答者,不予計分。

- 1. Explain the following noun. (20%)
 - a). Diamagentism
 - b). Antiferromagentism
 - c). Matthiessen Rule
 - d).Nordheim Rule
 - e).Hall coefficient
 - f). Wiedemann-Franz-Lorenz Law
 - g).Seebeck Effect
 - h).Peltier coefficient
 - i). Fick's first lass
 - i). Einstein relation
- 2. Copper (ion radius=0.125nm) and nickel (ion radius= 0.128nm) form a solid solution in all properties. Predict this result using the Hume-Rothery rules (15%)
- 3. At 200°C, a 50:50 Pb-Sn solder alloy exists as two phases, a lead-rich solid and a tin-rich liquid. Calculated the degree of freedom for this alloy (10%)
- 4. The fraction of vacant lattice sites in a crystal is typically small. For example, the fraction of aluminum sites vacant at 400°C is 2.29x10⁻⁵. Calculate the density of these sites (in unit of m⁻³). (the density of aluminum is 2.7Mg/m³ and its atomic mass is 26.98amu).(10%)
- 5. Please address what are the effect of temperature and impurity on the conductivity for metal, insulator and semiconductor, respectively.(20%)
- 6. Calculate the critical angle of incidence, θ_C in s step-index fiber design for a light ray going from a glass-fiber core (with index of refraction, n=1.47) to the cladding(with n=1.460). (10%)
- 7. For intrinsic gallium arsenide, the room temperature electrical conductivity is 10^{-6} $(\Omega-m)^{-1}$; the electron and hole mobilities are, respectively, 0.85 and 0.04 m²/V-s. Calculate the intrinsic carrier concentration n_i at room temperature. (15%)